



JLE12URF6-6

4-Line Low Capacitance Uni-directional TVS Diode

Jialan-Microelectronics

Description

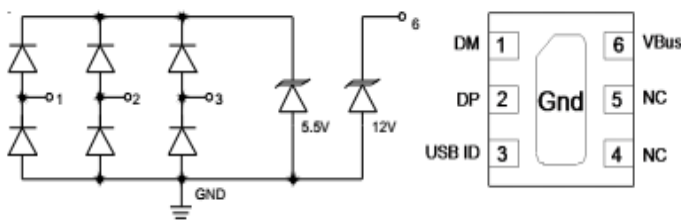
The JLE12URF6-6 is a low capacitance TVS array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines.

The JLE12URF6 -6 complies with the IEC 61000-4-2 (ESD) standard with ±25kV air and ±20kV contact discharge. It is assembled into a 6-pin DFN1616-6 lead-free package. The leads are finished with NiPdAu. Each device will protect up to four high-speed lines. The combination of small size, low capacitance, and high surge capability makes them ideal for use in applications such as USB ports.

Features

- * 100W peak pulse power (8/20µs)
- * Low leakage:nA level
- * Operating voltage: 12V
- * Low clamping voltage
- * Up to 3 lines and one power line protects
- * Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ±25kV
 - Contact discharge: ±20kV
 - IEC61000-4-5 (Lightning) 5A (8/20µs)
- * RoHS Compliant
- * Package: DFN1616-6

Circuit Diagram

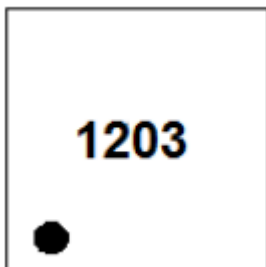


Circuit and Pin Schematic

Applications

- * USB2.0
- * USB OTG

Marking Diagram



Transparent top view

1203:Device Marking Code

Ordering Information

Part Number	Packaging	Reel Size
JLE12URF6-6	3000/Tape & Reel	7 inch



JLE12URF6-6

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
DP,DM,USB ID (Pins 1,2,3)			
Peak Pulse Power (8/20 μs)	Ppk	100	W
Peak Pulse Current (8/20 μs)	IPP	5	A
ESD per IEC 61000-4-2 (Air)	VESD	± 25	kV
ESD per IEC 61000-4-2 (Contact)		± 20	
Operating Temperature Range	TJ	-55to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$
VBus (Pins 6)			
Peak Pulse Power (8/20 μs)	Ppk	300	W
Peak Pulse Current (8/20 μs)	IPP	12	A
ESD per IEC 61000-4-2 (Air)	VESD	± 25	kV
ESD per IEC 61000-4-2 (Contact)		± 20	
Operating Temperature Range	TJ	-55to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DP,DM,USB ID TVS						
Reverse Working Voltage	V_{RWM}	Any I/O to ground			5.5	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$,any I/O to ground	6.5			V
Reverse Leakage Current	I_R	$V_{RWM} = 5.5\text{V}$,any I/O to ground			0.5	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 x 20 μs pulse), any I/O pin to ground			10	V
Clamping Voltage	V_C	$I_{PP} = 5\text{A}$ (8 x 20 μs pulse), any I/O pin to ground			20	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$,any I/O pins(1,2,3)			0.5	pF
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$,any I/O pin to ground			0.8	pF



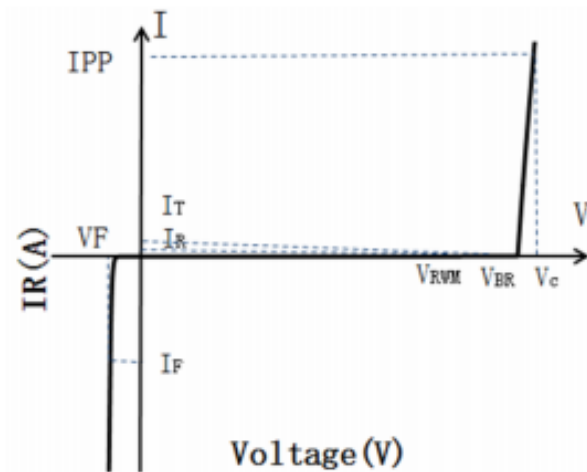
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
VBus TVS						
Reverse Working Voltage	V_{RWM}	Pin 6 to ground			12	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$, pin 6 to ground	13.3		18	V
Reverse Leakage Current	I_R	$V_{RWM} = 5.5\text{V}$, pin 6 to ground			0.2	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 x 20 μs pulse), pin 6 to ground			18	V
Clamping Voltage	V_C	$I_{PP} = 8\text{A}$ (8 x 20 μs pulse), pin 6 to ground			25	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$, pin 6 to ground			100	pF

Portion Electronics Parameter

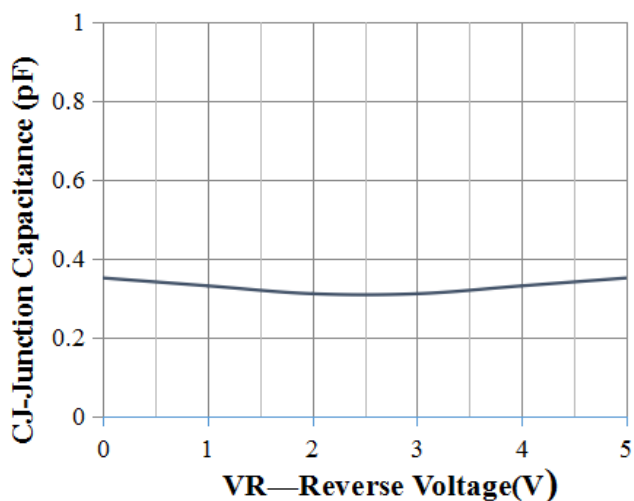
Symbol	Parameter
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_C



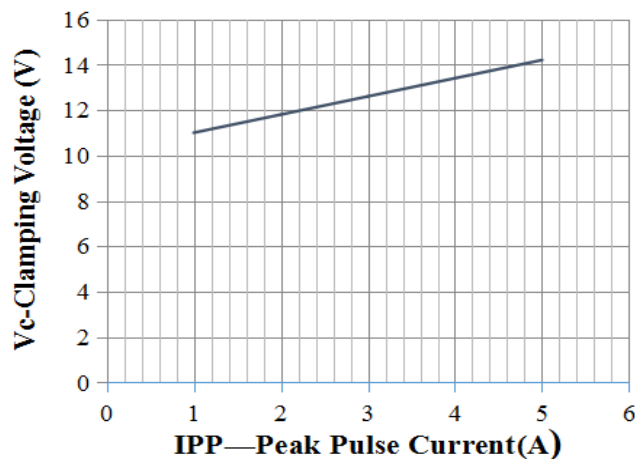


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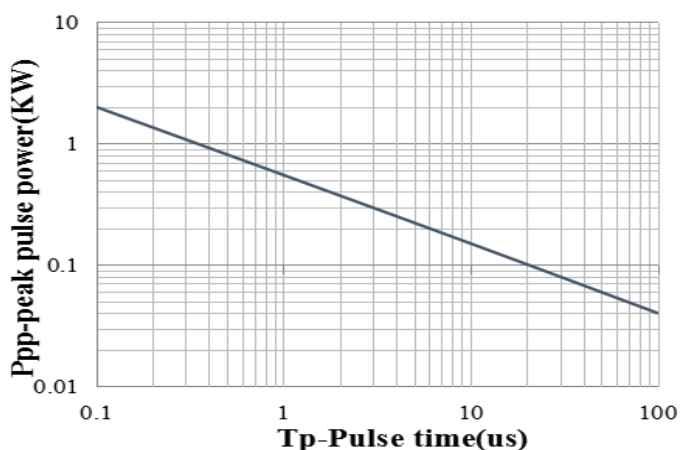
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



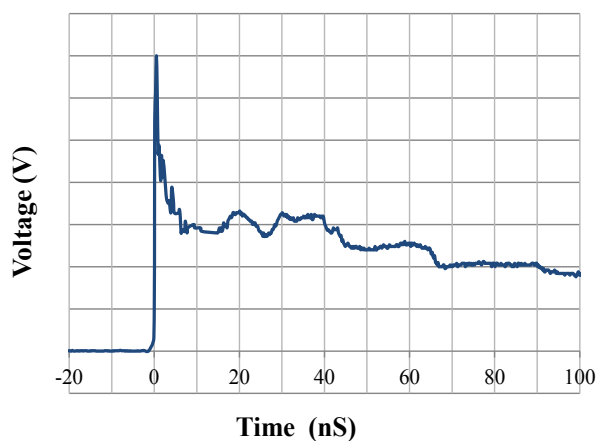
Junction Capacitance vs. Reverse Voltage



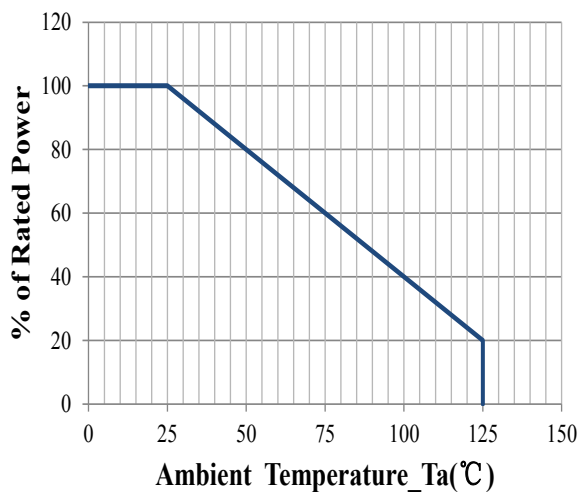
Clamping Voltage vs. Peak Pulse Current



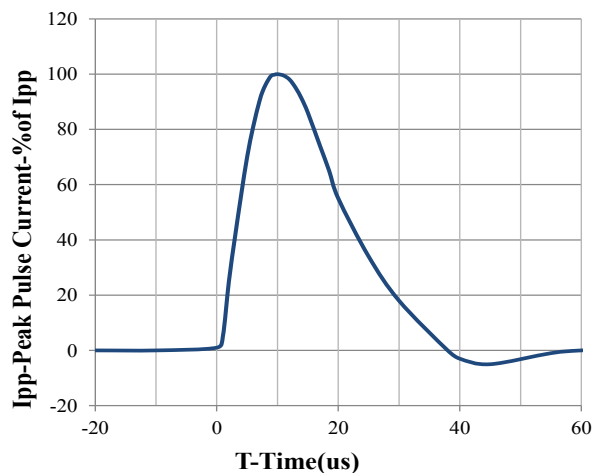
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform



Power Derating Curve

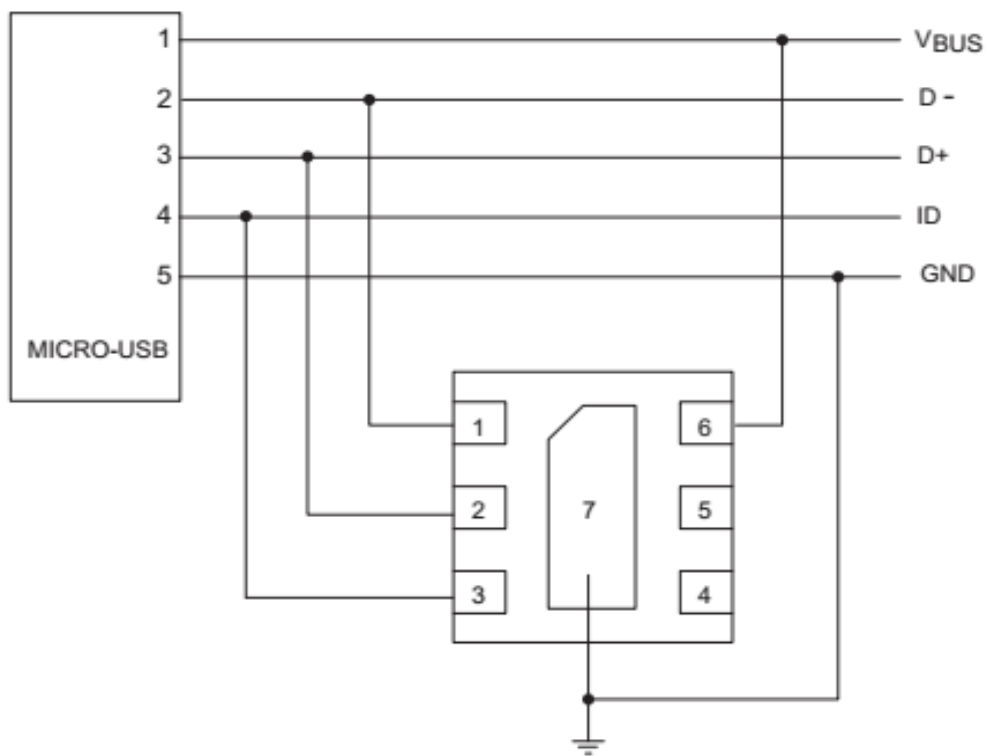


8 X 20us Pulse Waveform



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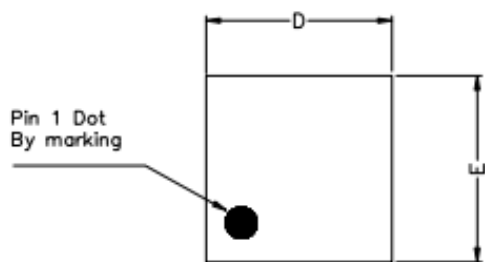
On USB Port Application



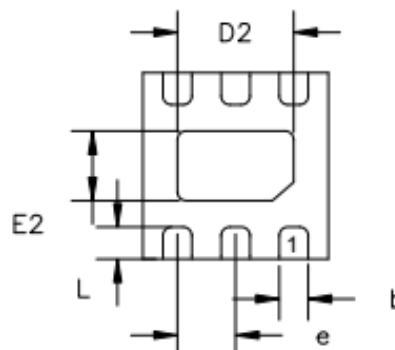


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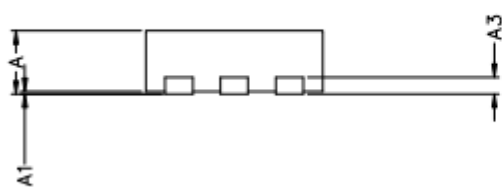
DFN1616-6 Package Outline Drawing (Dimensions in millimeters)



TOP VIEW



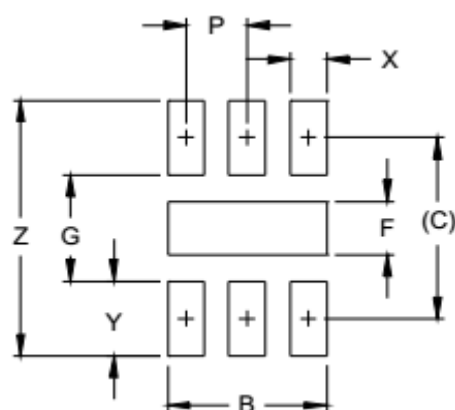
BOTTOM VIEW



SIDE VIEW

PKG. REF.	COMMON DIMENSIONS(MM)		
	MIN.	UT:ULTRA THIN NOM.	MAX
A	0.50	0.55	0.60
A1	0.00	-	0.05
A3	0.15 REF.		
D	1.55	1.60	1.65
E	1.55	1.60	1.65
D2	0.90	1.00	1.05
E2	0.50	0.60	0.65
L	0.20	0.25	0.30
b	0.20	0.25	0.30
e	0.50 BSC		

Suggested Land Pattern



DIM	DIMENSIONS	
	INCHES	MILLIMETERS
B	.051	1.30
C	.060	1.52
P	.020	0.50
F	.018	0.45
G	.035	0.89
X	.012	0.30
Y	.025	0.63
Z	.085	2.15

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